

2N4400

MMBT4400





NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N4400	*MMBT4400	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

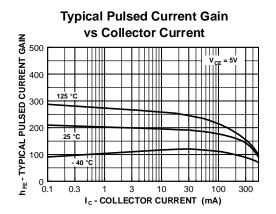
NPN General Purpose Amplifier (continued)

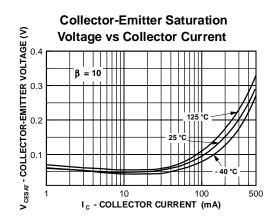
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	6.0		V
I _{CEX}	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, \ V_{EB} = 0.4 \text{ V}$		0.1	μΑ
I _{BL}	Emitter Cutoff Current	$V_{CE} = 35 \text{ V}, \ V_{EB} = 0.4 \text{ V}$		0.1	μΑ
ON CHAF	RACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	20		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	40		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 150 \text{ mA}$	50	150	
\/	Collector-Emitter Saturation Voltage	$V_{CE} = 2.0 \text{ V}, I_{C} = 500 \text{ mA}$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$	20	0.40	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.40	V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 150 mA, I _B = 15 mA	0.75	0.95	V
DL(Gat)		I 500 A I 50 A			
		$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.2	V
		I _C = 500 mA, I _B = 50 mA		1.2	V
SMALL S	SIGNAL CHARACTERISTICS	I _C = 500 mA, I _B = 50 mA		1.2	V
	SIGNAL CHARACTERISTICS Output Capacitance	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$		6.5	V
SMALL S C _{ob}					
C _{ob}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$	2.0	6.5	pF
C _{ob} C _{ib}	Output Capacitance Input Capacitance	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$	2.0	6.5	pF
C _{ob} C _{ib} h _{fe}	Output Capacitance Input Capacitance Small-Signal Current Gain	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	_	6.5	pF
C _{ob} C _{ib} h _{fe} h _{ie}	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$	20	6.5 30 250	pF pF
Cob Cib hfe hfe hie hre	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$	20	6.5 30 250 7.5	pF pF
C _{ob}	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$	20 0.5 0.1	6.5 30 250 7.5 8.0	pF pF ΚΩ x 10 ⁻⁴
Cob Cib hfe hfe hie hre	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$	20 0.5 0.1	6.5 30 250 7.5 8.0	pF pF ΚΩ x 10 ⁻⁴
Cob Cib hfe hfe hie hre	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$	20 0.5 0.1	6.5 30 250 7.5 8.0	pF pF ΚΩ x 10 ⁻⁴
C _{ob} C _{ib} h _{fe} h _{fe} h _{ie} h _{re} h _{oe}	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance	$V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$ $f = 1.0 \text{ kHz}$	20 0.5 0.1	6.5 30 250 7.5 8.0 30	pF pF KΩ x 10 ⁻⁴ μmhos
Cob Cib hfe hfe hie hoe	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance NG CHARACTERISTICS Delay Time	$V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, } f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, } f = 1.0 \text{ kHz}$ $V_{CC} = 30 \text{ V, } I_{C} = 150 \text{ mA, } f = 100 \text{ mA, } f = 10$	20 0.5 0.1	6.5 30 250 7.5 8.0 30	pF pF KΩ x 10 ⁻⁴ μmhos

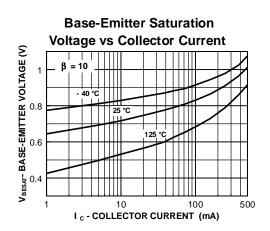
^{*}Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0%

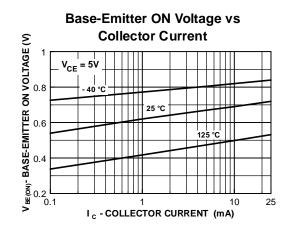
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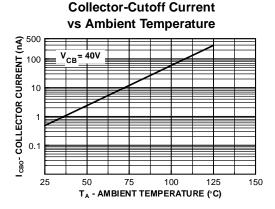
Typical Characteristics

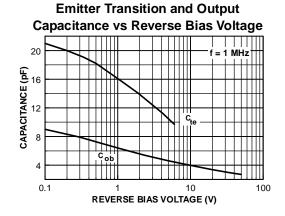








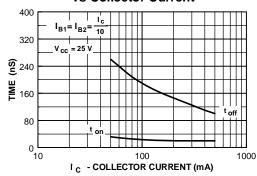




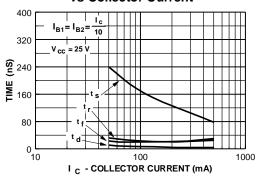
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Typical Characteristics (continued)

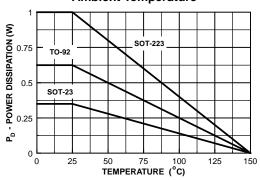
Turn On and Turn Off Times vs Collector Current



Switching Times vs Collector Current

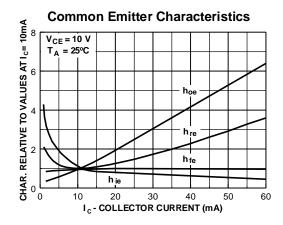


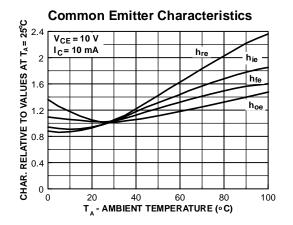
Power Dissipation vs Ambient Temperature

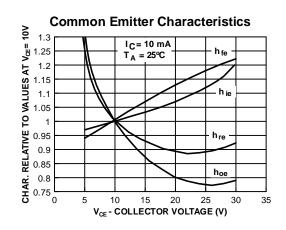


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Typical Common Emitter Characteristics (f = 1.0kHz)







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Test Circuits

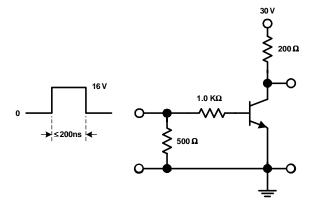


FIGURE 1: Saturated Turn-On Switching Timer

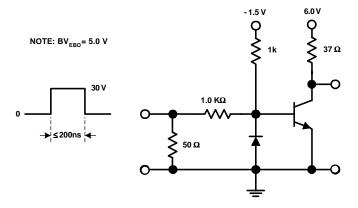


FIGURE 2: Saturated Turn-Off Switching Time

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Definition of Terms

Datasheet Identification	Product Status	Definition
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NPN General Purpose Amplifier

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General description

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA.

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BUY

Product	Product status	Pb-free Status	Pricing*	Package type	Leads	Packing method	Package Marking Convention**
2N4400BU	Full Production	Full Production	\$0.026	<u>TO-92</u>	3	BULK	Line 1: 2N Line 2: 4400 Line 3: -&3
2N4400TA	Full Production	Full Production	\$0.026	<u>TO-92</u>	3	AMMO	Line 1: 2N Line 2: 4400 Line 3: -&3
2N4400TAR	Full Production	Full Production	\$0.026	<u>TO-92</u>	3	AMMO	Line 1: 2N Line 2: 4400 Line 3: -&3
2N4400TF	Full Production		\$0.026	<u>TO-92</u>	3	TAPE REEL	Line 1: 2N Line 2: 4400 Line 3: -&3

		Full Production					
2N4400TFR	Full Production	Full Production	\$0.026	<u>TO-92</u>	3	TAPE REEL	Line 1: 2N Line 2: 4400 Line 3: -&3
2N4400_D81Z	Full Production	Full Production	N/A	<u>TO-92</u>	3	TAPE REEL	Line 1: \$Y (Fairchild logo) & Z (Asm. Plant Code) & 3 (3-Digit Date Code) Line 2: 2N Line 3: 4400

^{*} Fairchild 1,000 piece Budgetary Pricing

** A sample button will appear if the part is available through Fairchild's on-line samples program. If there is no sample button, please contact a Fairchild distributor to obtain samples



Indicates product with Pb-free second-level interconnect. For more information click here.

Package marking information for product 2N4400 is available. Click here for more information.

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Models

Package & leads Condition Temperature range		Temperature range	Software version	Revision date		
	PSPICE					
TO-92-3 <u>Electrical</u> 25°C N/A N/A				N/A		

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Qualification Support

Click on a product for detailed qualification data

Product
<u>2N4400BU</u>
<u>2N4400TA</u>
2N4400TAR
2N4400TF
<u>2N4400TFR</u>

2N4400_D81Z

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